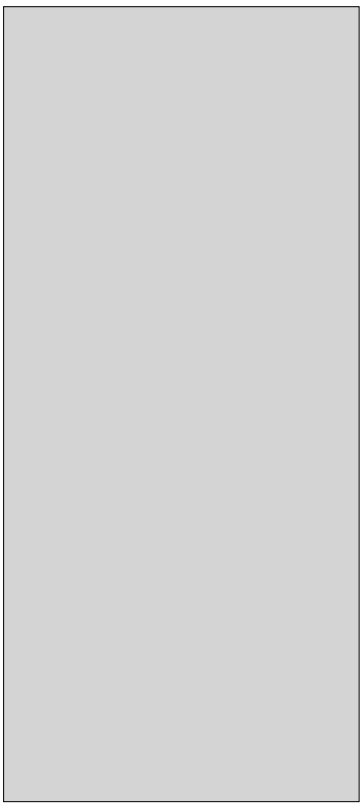
JCT151F-800R



Peak gate current (t_p=20μs , T_j=125)	I_{GM}	4	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	0.2	-	-	V
I_L	I_G=1.2I_{GT}	-	-	40	mA

N = Q ' 5 =12

ORDERING INFORMATION

J	CT	151	F	-800R
JieJie Microelectronics Co.,Ltd.	SCRs	$I_{T(RMS)}$:12A	F:TO-220F(Ins)	800R:V_{DRM} /V_{RRM} ≥ 800V

MARKING

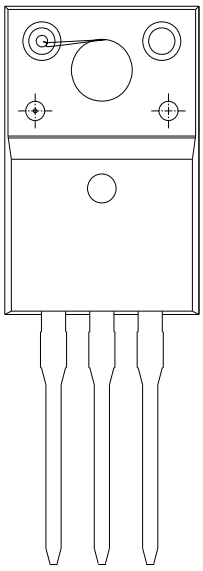


FIG.1: Maximum power dissipation versus RMS on-state current

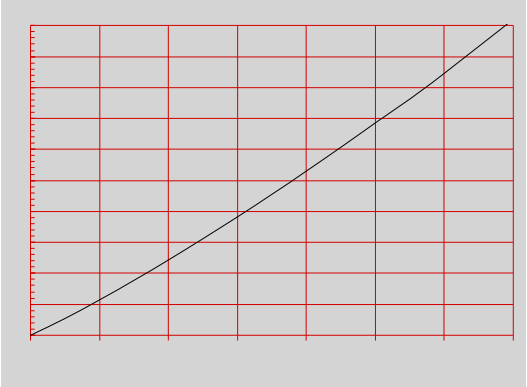


FIG.2: RMS on-state current versus case temperature

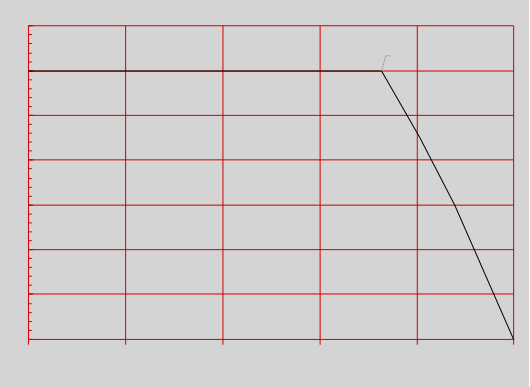
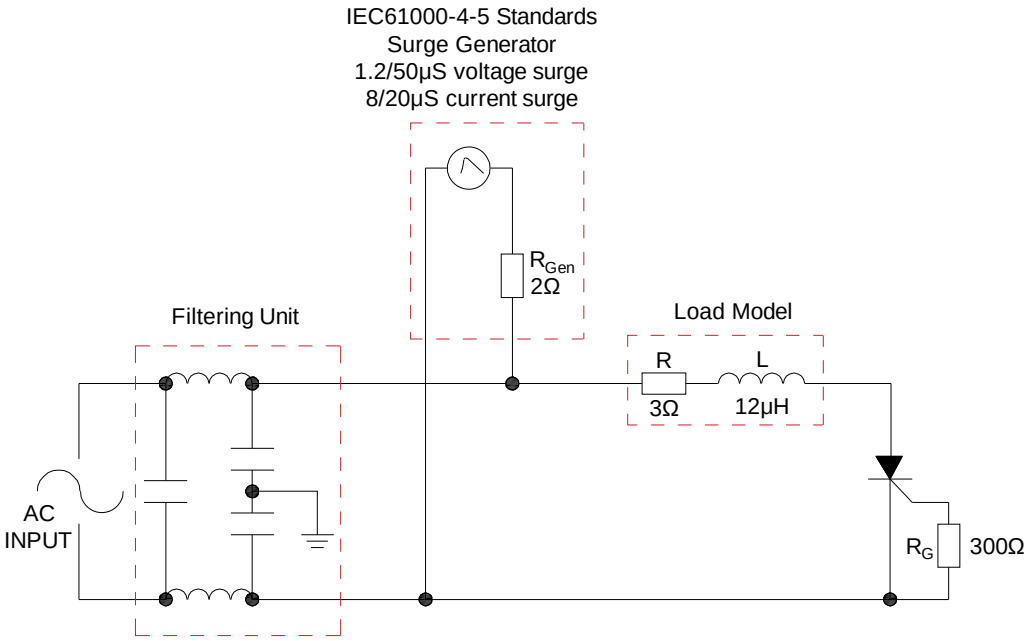


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT151F-800R	800	15	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update
Sept.28, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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